

Patent Abstracts of Japan

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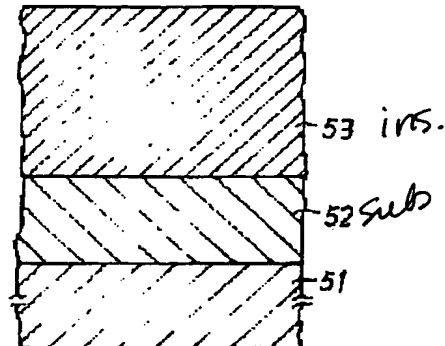
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TITLE : MANUFACTURE OF
SEMICONDUCTOR DEVICE AND
MANUFACTURING DEVICE



ABSTRACT : PURPOSE: To form a film, which is good in burying properties and at the same time, has no void and moreover, shows a low water content in the film and is superior in film quality, as an insulating film.

CONSTITUTION: In the case where an insulating film 53, which is a semiconductor layer, is formed, the surface of a substrate 52 is first treated with an organic compound and thereafter, the film 53 is formed by a chemical vapor deposition method using an organic silicon compound as a raw material. After this film 53 is formed, a post-treatment consisting of a plasma treatment and a UV-O₃ or annealing treatment is performed. In such a way, the substrate is treated with the organic compound and after the film 53 is formed, the post-treatment is performed, whereby a water content in the film 53 can be effectively reduced.

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